

Vertical WSe₂ -MoSe₂ p-n heterostructure with tunable gate rectification

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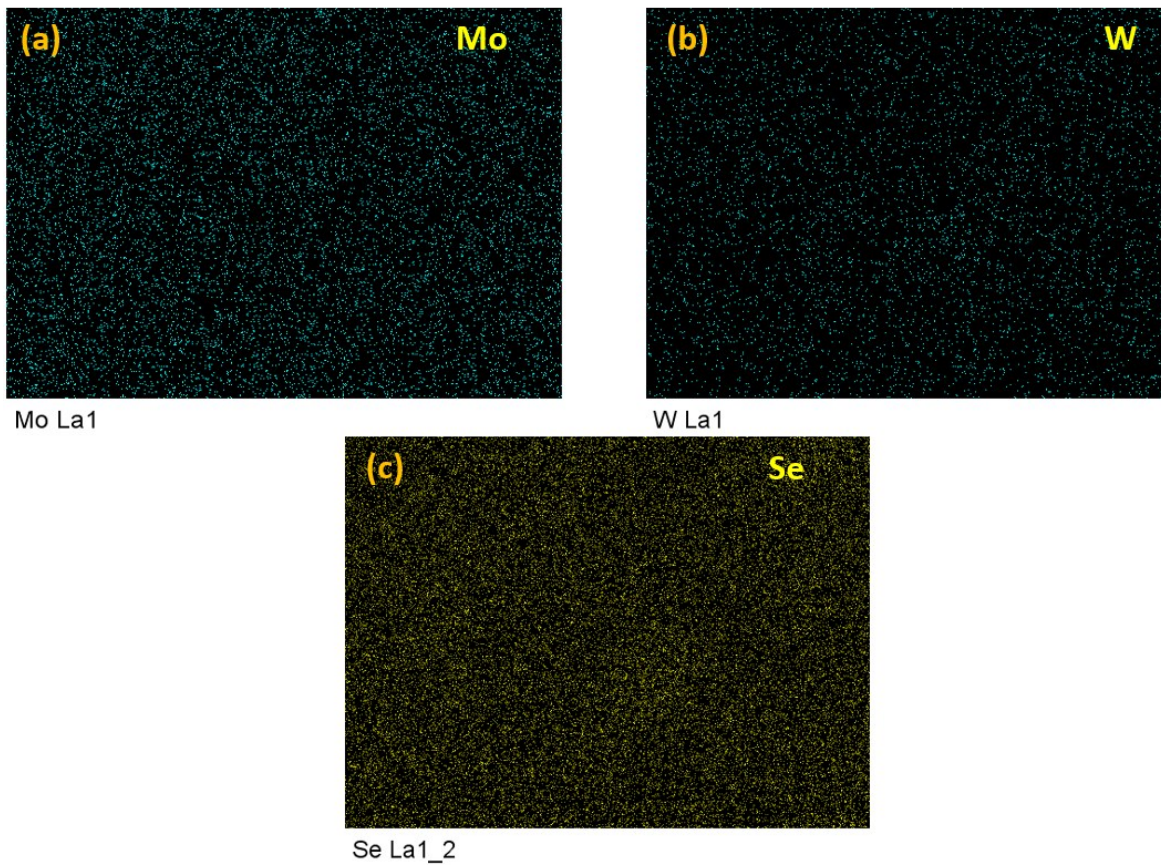


Figure S1. **(a-c)** FESEM elemental mapping images of $WSe_2/MoSe_2$ (a) Mo, (b) W and (c) Se elements.

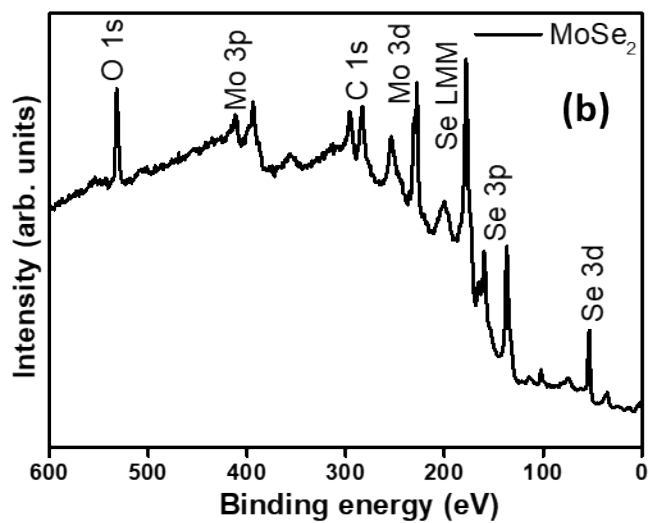
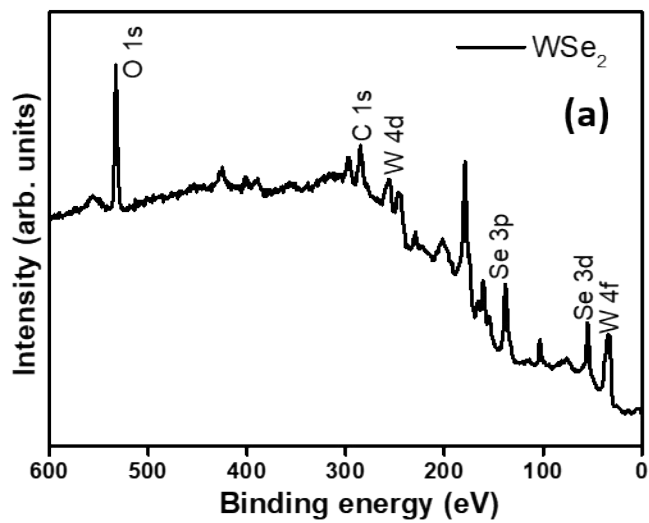


Figure S2. XPS survey scans for (a) WSe_2 and (b) MoSe_2 .

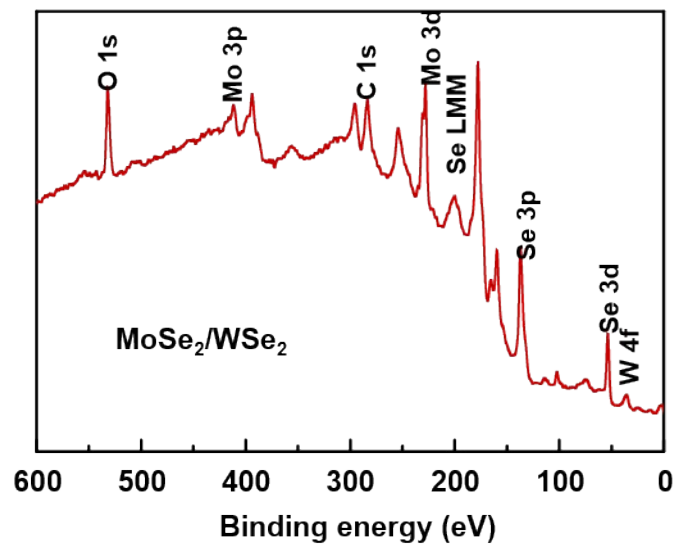


Figure S3. XPS survey scans of MoSe₂/WSe₂ heterostructure.